

AlGaInP OMVPE Epitaxial Wafers

Feature

- Excellent uniformity, Precise epitaxial structure.
- Various hetero-structures are available on request.

Application

- Laser Diode for DVD

Standard Specifications

Application		Laser Diode
Structure		⑤ p-GaAs
		④ p-GaInP
		③ p-AlGaInP
		② MQW
		① n-AlGaInP
		n-GaAs Sub.
Epi.	⑤ C.C. (cm ⁻³)	>1×10 ¹⁸
	Thickness (μm)	0.5~1
	④ C.C. (cm ⁻³)	on request
	Thickness (μm)	0.5~1×10 ¹⁸ 0.5~1
	③ C.C. (cm ⁻³)	0.5~1×10 ¹⁸ 0.5~1
Sub.	② C.C. (cm ⁻³)	on request
	Thickness (μm)	on request
	① C.C. (cm ⁻³)	1~2×10 ¹⁸
	Thickness (μm)	0.5~1
	Size	2"φ, 3"φ
Sub.	Thickness (μm)	340~360, 430~470
	Dopant	Si
	C.C. (cm ⁻³)	1~2×10 ¹⁸
	EPD	≤2000
	Orientation	on request